# IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Barclay et al.

EXPRESS MAIL LABEL NO .:

FILED:

**HEREWITH** 

FOR:

NOVEL POLYMERS AND PHOTORESIST COMPOSITIONS

THE HONORABLE COMMISSIONER OF PATENTS AND TRADEMARKS WASHINGTON, DC 20231

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## PRELIMINARY AMENDMENT

Applicants file the above-identified application herewith. Please amend the application as follows.

# IN THE SPECIFICATION

At page 1, line 1 of text, please add the following sentence:

-- The present application claims the benefit of U.s. provisional application number 60/271,404,filed February 25, 2001, which is incorporated herein by reference in its entirety.--

### IN THE CLAIMS

Please cancel without prejudice claims 13-14 and 17-25.

Please amend the following claims.

3. (amended) A photoresist of claim 1 wherein the resin comprises photoacid-labile groups.

- 5. (amended) A photoresist of claim 2 wherein the resin comprises a photoacid-labile ester group.
- 6. (amended) A photoresist of claim 1 wherein the resin comprises a polymerized cyclic olefin.
- 7. (amended) A photoresist of claim 1 wherein the resin comprises a polymerized monomer comprising ethylene unsaturated carbonyl or di-carbonyl.
  - 8. (amended) A photoresist of claim 1 wherein the resin is a terpolymer.
- 9. (amended) A photoresist of any one of claim 1 wherein the resin is a tetrapolymer.
- 10. (amended) The photoresist of claim 1 wherein the polymer further comprises one or more units selected from the group consisting of an acid; nitrile; an anhydride; a lactone; or a photoacid labile group that contains a leaving group that has other than an alicyclic moiety.
- 11. (amended) The photoresist of claim 1 wherein the polymer is substantially of aromatic groups.
- 12. (amended) A method of forming a positive photoresist relief image, comprising:
  - (a) applying a coating layer of a photoresist of claim 1 on a substrate; and
  - (b) exposing and developing the photoresist layer to yield a relief image.

15. An article of manufacture comprising a microelectronic wafer substrate or flat panel display substrate having coated thereon a layer of the photoresist composition of any one of claim 1.

#### **REMARKS**

The specification has been amended to include the priority claim. For the sole purpose of reducing initial filing fees, claims 13-14 and 17-25 have been cancelled without prejudice, and claims 3, 5-12 and 15 have been amended to eliminate multiple dependencies.

Early consideration and allowance of the application are solicited.

Respectfully submitted,

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#### VERSION WITH CHANGES MARKED

3.	(amended)	A photoresist of claim 1 [or 2] wherein the resin comprises
photoacid-la	ibile groups.	

- 5. (amended) A photoresist of claim 2 [or 3] wherein the resin comprises a photoacid-labile ester group.

  6. (amended) A photoresist of claim 1 [any one of claims 1 through 5] wherein the resin comprises a photoacid-labile ester group.
- 6. (amended) A photoresist of <u>claim 1</u> [any one of claims 1 through 5] wherein the resin comprises a polymerized cyclic olefin.
- 7. (amended) A photoresist of <u>claim 1</u> [any one of claims 1 through 6] wherein the resin comprises a polymerized monomer comprising ethylene unsaturated carbonyl or difficarbonyl.
  - 8. (amended) A photoresist of <u>claim 1</u> [any one of claims 1 through 7] wherein the resin is a terpolymer.
  - 9. (amended) A photoresist of any one of <u>claim 1</u> [claims 1 through 8] wherein the resin is a tetrapolymer.
  - 10. (amended) The photoresist of <u>claim 1</u> [any one of claims 1 through 9] wherein the polymer further comprises one or more units selected from the group consisting of an acid; nitrile; an anhydride; a lactone; or a photoacid labile group that contains a leaving group that has other than an alicyclic moiety.

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- The photoresist of claim 1 [any one of claims 1 through 11] 11. (amended) wherein the polymer is substantially of aromatic groups.
- A method of forming a positive photoresist relief image, 12. (amended) comprising:
- applying a coating layer of a photoresist of claim 1 [any one of claims 1 through (a) 11] on a substrate; and
- (b) exposing and developing the photoresist layer to yield a relief image.

  15. An article of manufacture comprising a microelectronic wafer substrate or flat panel display substrate having coated thereon a layer of the photoresist composition of any one Cof claim 1 [claims 1 through 11].